

Anisotropy of radiation-induced defects in Yb-implanted β -Ga₂O₃

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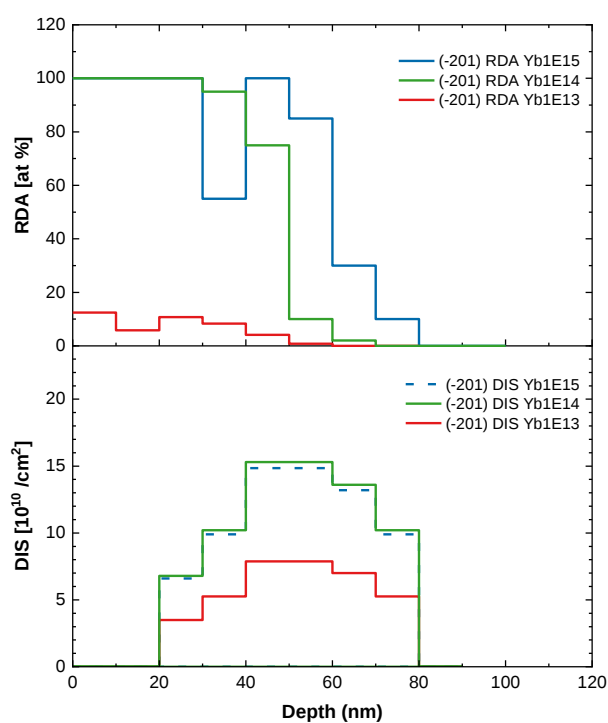


Figure 1 SM. Distribution of simple (RDA) and extended (DIS) defects obtained by McChasy simulations for (-201) oriented β -Ga₂O₃ implanted with Yb-ions of different fluences.

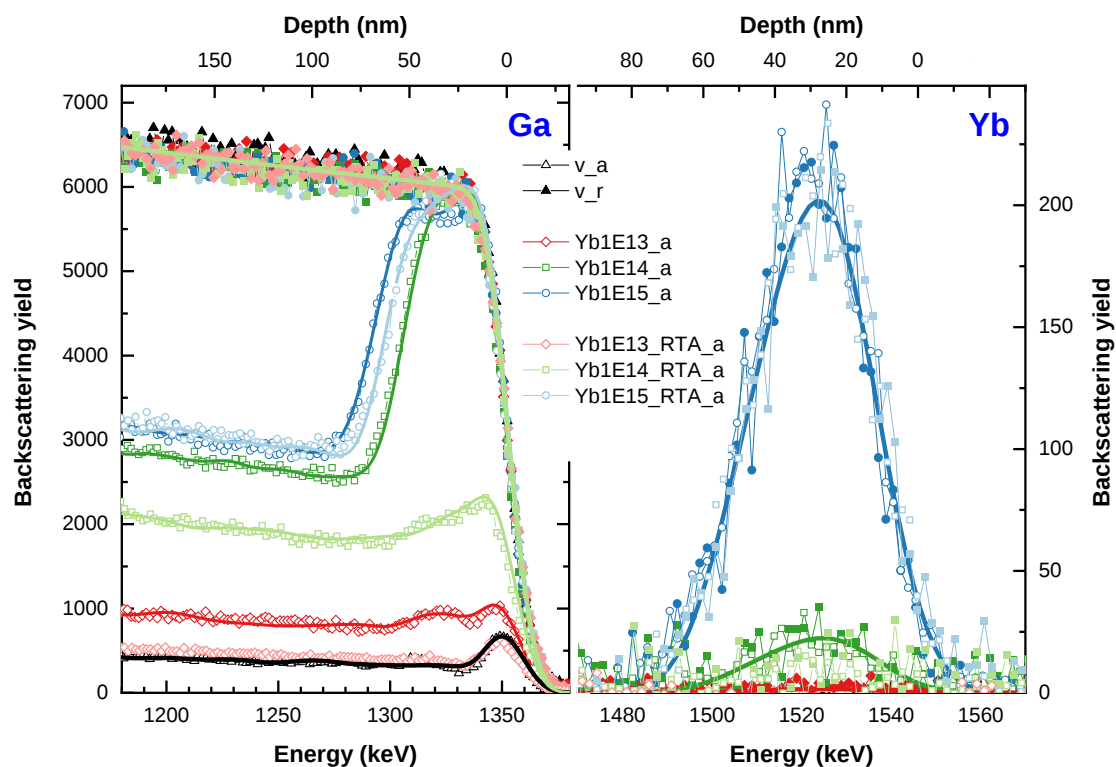


Figure 2 SM. Random (solid symbols) and aligned (open symbols) RBS experimental spectra obtained for (-201) oriented β -Ga₂O₃ single crystals implanted with different fluences of Yb ions and annealed in O₂ at 800°C for 10min.

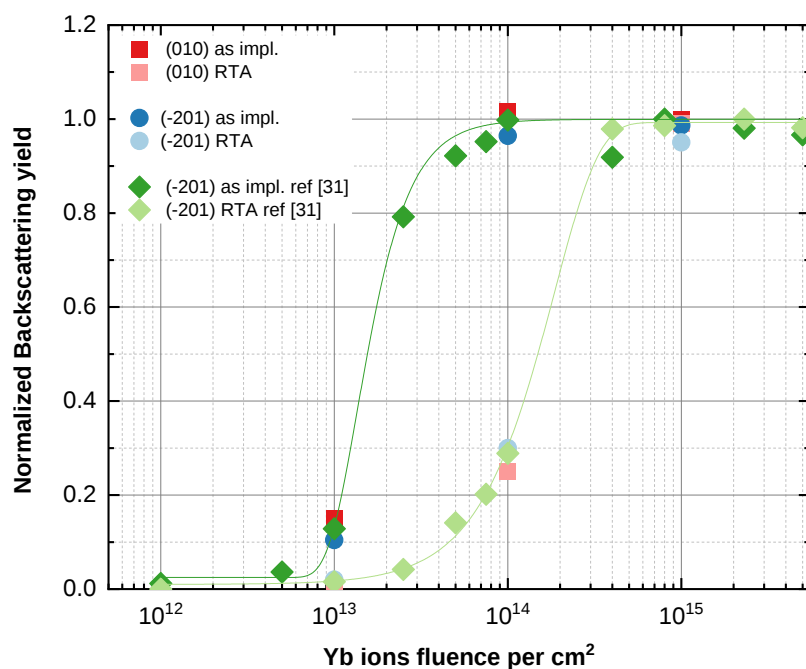


Figure 3 SM. Dependence of the backscattering yield (normalized to the random level) in the damage zone for (-201) and (010) oriented β -Ga₂O₃ implanted with Yb and post-implantation annealed for 10 min at 800 °C in O₂, measured for the aligned spectra at the energy region of 1325-1352 keV and normalized to the random level.

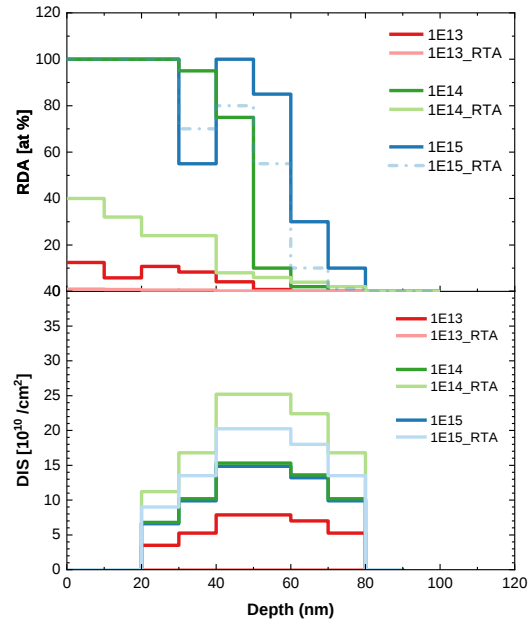


Figure 4 SM. Distribution of simple (RDA) and extended (DIS) defects obtained by McChasy simulations for (-201) oriented β -Ga $_2$ O $_3$ single crystals implanted with different fluences of Yb ions and annealed in O $_2$ at 800°C for 10min